Supporting Information

Polystyrene-Block-Poly (methylmethacrylate) Composite Materials Film as a Gate Dielectric for Plastic Thin-Film Transistor Applications

Jagan Singh Meena\textsuperscript{ab}, Min-Ching Chu\textsuperscript{a}, Ranjodh Singh\textsuperscript{a}, Chung-Shu Wu\textsuperscript{a}, Umesh Chand\textsuperscript{b}, Hsin-Chiang You\textsuperscript{c}, Po-Tsun Liu\textsuperscript{a}, Han-Ping D. Shieh\textsuperscript{a} and Fu-Hsiang Ko\textsuperscript{a*}

\textsuperscript{a}Department of Materials Science and Engineering, Department of Photonics and Display Institute, National Chiao Tung University, Hsinchu 30010, ROC, Taiwan

\textsuperscript{b}Department of Electronics Engineering, National Chiao Tung University, Hsinchu 30010, ROC, Taiwan

\textsuperscript{c}Department of Electronic Engineering, National Chin–Yi University of Technology, Taichung 41170, ROC, Taiwan.

*E-mail: fhko@mail.nctu.edu.tw
**Figure S1.** Leakage current density measurements test for 1 day to 4 weeks for double layer PS–b–PMMA film (28 nm thick) as dielectric layer in MIM structured device.
Figure S2. Transfer characteristic ($I_{DS}-V_{GS}$), when $V_{DS}=10$ V for double layer PS–$b$–PMMA film (28 nm thick) as gate dielectric layer and ZnO as semiconductor active layer for day 1 to 4 weeks.